Transistors

## 2SC1384

## Silicon NPN epitaxial planar type

For low-frequency power amplification and driver amplification Complementary to 2SA0684

#### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Complementary pair with 2SA0684

### $\blacksquare$ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V	
Collector current	$I_{C}$	1	A	
Peak collector current	$I_{CP}$	1.5	A	
Collector power dissipation	P <sub>C</sub>	1	W	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C ,	

#### ■ Package

- Code
  - TO-92L-A1
- Pin Name
  - 1. Emitter
  - 2. Collector
  - 3. Base

### ■ Electrical Characteristics $T_a = 25$ °C±3°C

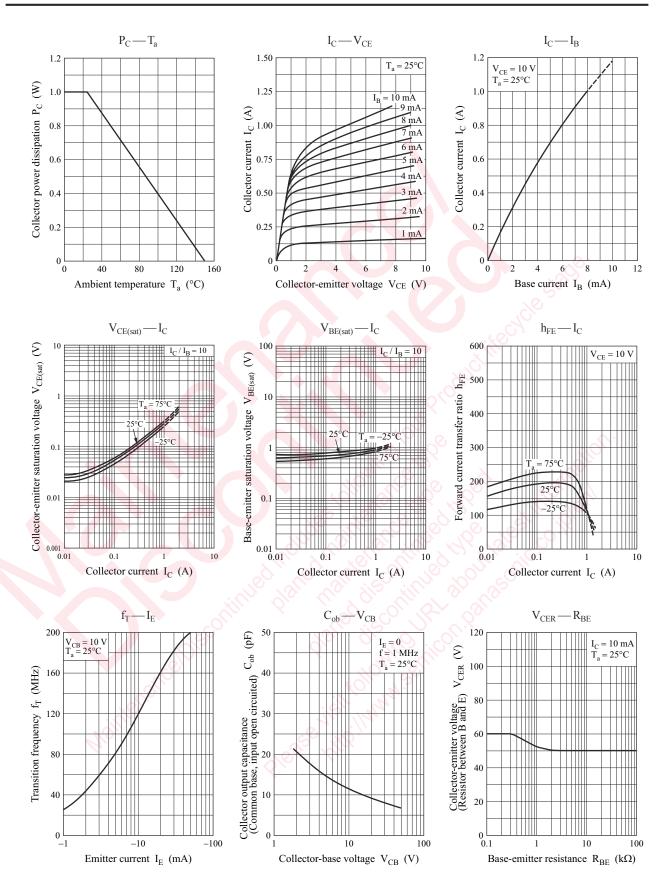
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_{\rm C} = 10  \mu A, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50	Ö <sub>()</sub>		V
Emitter-base voltage (Collector open)	$V_{\mathrm{EBO}}$	$I_E = 10 \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_{E} = 0$	60		0.1	μΑ
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	85		340	
	h <sub>FE2</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	50			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2	0.4	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.85	1.20	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>re</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		11	20	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. \*1: Pulse measurement
  - \*2: Rank classification

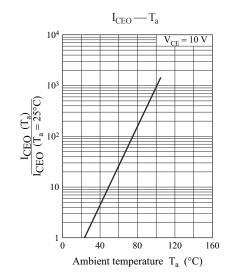
Rank	Q	R	S
$h_{\rm FE1}$	85 to 170	120 to 240	170 to 340

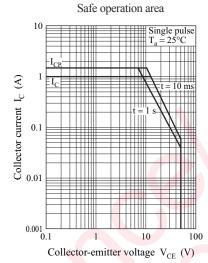
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Panasonic 2SC1384

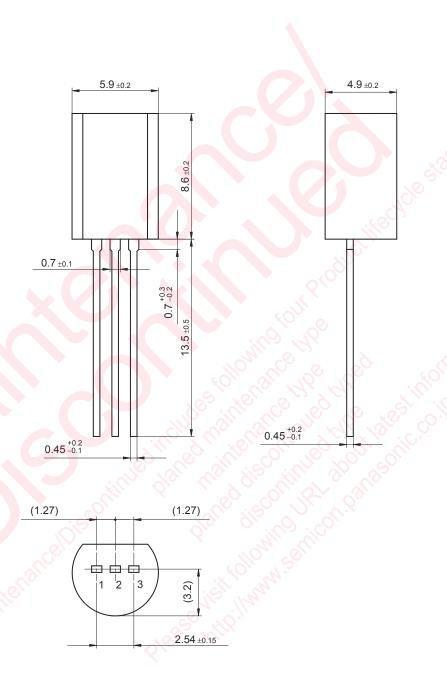




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**Panasonic** 

TO-92L-A1 Unit: mm



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